

**In the Specification**

Please amend paragraph [0031] as shown:

In addition, Figure 4 illustrates a process of forming the source and drain regions as shown at 410 and 420. Since a sacrificial gate ~~of having a polysilicon layer 260~~ is used, the substrate 200 can also be doped to form the source and drain regions 410 and 420 in the active area 240. The doping involves the implantation of ions into the substrate to alter the conductivity of the source and drain regions 410 and 420. Polysilicon, as mentioned above, has the ability to block such implantation to the channel region, ~~shown at 450 in Figure 4.~~

Please amend paragraph [0051] as shown:

In addition, TiN and other diffusion barrier layers have more conformal properties which avoid the problems caused by the non-conformal nature of a tungsten layer deposited from a W(CO)<sub>6</sub> precursor. This particularly addresses the problems of pinch-off and formation of a void in the middle of the gate that arises during deposition of tungsten from a W(CO)<sub>6</sub> precursor. This is due to the fact that the tungsten deposition from the WF<sub>6</sub> precursor fills the opening more conformally, from the sidewalls 810-920 of the opening rather than from other directions.

Please amend paragraph [0053] as shown:

Figure 10 is an illustration of the resultant metal gate 1000 formed in a preferred embodiment of the invention. As shown in Figure 10, the resultant metal gate 1000 includes a first layer of metal or metal compound 700 in contact with the gate dielectric 650750, a diffusion barrier layer 800 such as the preferred structure of titanium-TiN here and an overlying layer 900 of metal, such as tungsten. When the metal gate includes tungsten as the first and third layers 700, 900, it operates much like a gate formed entirely of tungsten but without some of the problems that plague the fabrication and performance of a gate formed entirely of tungsten. In a particular embodiment, at least one of the first layer 700 and the third layer 900 includes an impurity concentration which adjusts the metal gate 1000 to a desired workfunction.